2N6605
2N6606
2N6607
2N6608

SILICON CONTROLLED RECTIFIER
0.35 AMP, 30 THRU 200 VOLTS

TO-18 CASE

Central Semiconductor Corp.

www.centralsemi.com

DESCRIPTION:

The CENTRAL SEMICONDUCTOR 2N6605 Series types are hermetically sealed silicon controlled rectifiers manufactured in a TO-18 case, designed for control systems and sensing circuit applications.

MARKING: FULL PART NUMBER

MAXIMUM RATINGS: (T_C=25°C)	**SYMBOL**	**2N6605**	**2N6606**	**2N6607**	**2N6608**	**UNITS**
Peak Repetitive Off-State Voltage	V_{DRM}, V_{RRM}	30	60	100	200	V
Average On-State Current	I_O		0.35			A
Peak One Cycle Surge Current (t=8.3ms)	I_{TSM}		6.0			A
Peak Gate Voltage	V_{GM}		8.0			V
Operating Junction Temperature	T_J		-40 to +125			°C
Storage Temperature	T_{stg}		-40 to +150			°C

ELECTRICAL CHARACTERISTICS: (T_C=25°C unless otherwise noted)

SYMBOL	**TEST CONDITIONS**	**MIN**	**MAX**	**UNITS**
I_{DRM}	Rated V_{DRM}, R_{GK}=1.0KΩ		120	nA
I_{RRM}	Rated V_{RRM}		250	nA
I_{GT}	V_D=6.0V, R_L=100Ω		200	μA
V_{GT}	V_D=6.0V, R_L=100Ω		0.8	V
V_{TM}	I_T=2.0A		2.0	V
I_H	R_{GK}=1.0KΩ		5.0	mA

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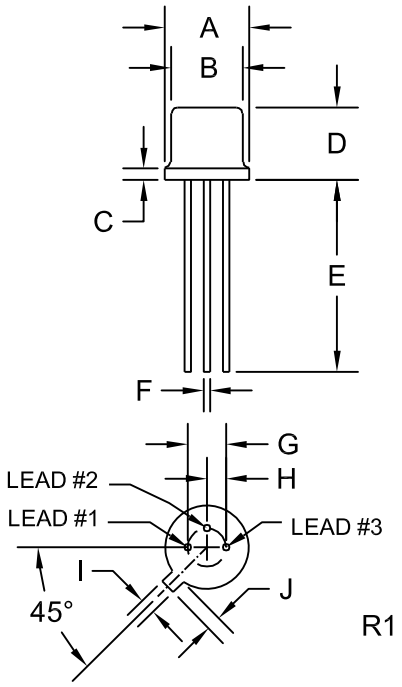
TO-18 CASE - MECHANICAL OUTLINE



DIMENSIONS				
	INCHES		MILLIMETERS	
SYMBOL	MIN	MAX	MIN	MAX
A (DIA)	0.209	0.230	5.31	5.84
B (DIA)	0.178	0.195	4.52	4.95
C	-	0.030	-	0.76
D	0.170	0.210	4.32	5.33
E	0.500	-	12.70	-
F (DIA)	0.016	0.019	0.41	0.48
G (DIA)	0.100		2.54	
H	0.050		1.27	
I	0.036	0.046	0.91	1.17
J	0.028	0.048	0.71	1.22

TO-18 (REV: R1)

LEAD CODE:
1) Cathode
2) Gate
3) Anode

MARKING: FULL PART NUMBER